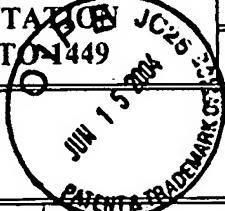


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### U.S. PATENT DOCUMENTS

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Examiner	Date Considered 04/05/2005